#### Transistors

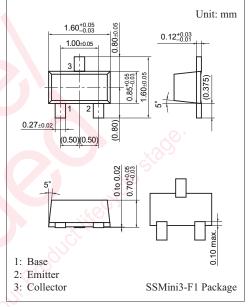
# 2SA2174J

### Silicon PNP epitaxial planar type

For general amplification Complementary to 2SC6054J

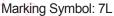
#### Features

- High forward current transfer ratio  $h_{FE}$
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.



#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit					
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-60	V					
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V					
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	-7	v					
Collector current	I <sub>C</sub>	-100	mA					
Peak collector current	I <sub>CP</sub>	-200	mA					
Collector power dissipation	P <sub>C</sub>	125	mW					
Junction temperature	Tj	125	°C					
Storage temperature	T <sub>stg</sub>	-55 to +125	°C					
Electrical Characteristics $T_{r} = 25^{\circ}C + 3^{\circ}C$								



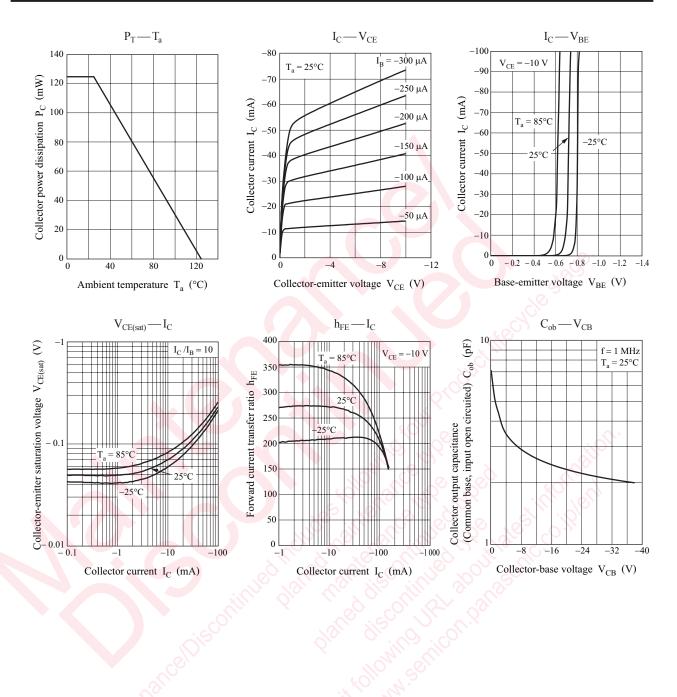
#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_{\rm E} = -10 \ \mu \text{A}, I_{\rm C} = 0$	- 7			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -10 \text{ V}, I_B = 0$			-100	μΑ
Forward current transfer ratio	$h_{\mathrm{FE}}$	$V_{CE} = -10 \text{ V}, I_C = -2 \text{ mA}$	160		460	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -100 \text{ mA}, I_{\rm B} = -10 \text{ mA}$		- 0.2	- 0.5	V
Transition frequency	$f_{T}$	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2.2		pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

#### 2SA2174J

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